

Abstract of the Disclosure

The gate resistance of a power MOSFET in a semiconductor chip is reduced and the reliability and yield of the gate of the power MOSFET are improved. The semiconductor chip includes two or more control electrode pads functioning as control electrodes for a power semiconductor device formed within a semiconductor chip. The two or more control electrode pads are distributed within the periphery of the gate area of the power semiconductor device such that the gate resistance of the power semiconductor device can be reduced. The two or more control electrode pads are connected via bumps or a conductive bonding material to an electrode layer of a multilayer circuit board disposed outside the semiconductor chip.